



# BYW81G-200 BYW81P-200 / BYW81PI-200

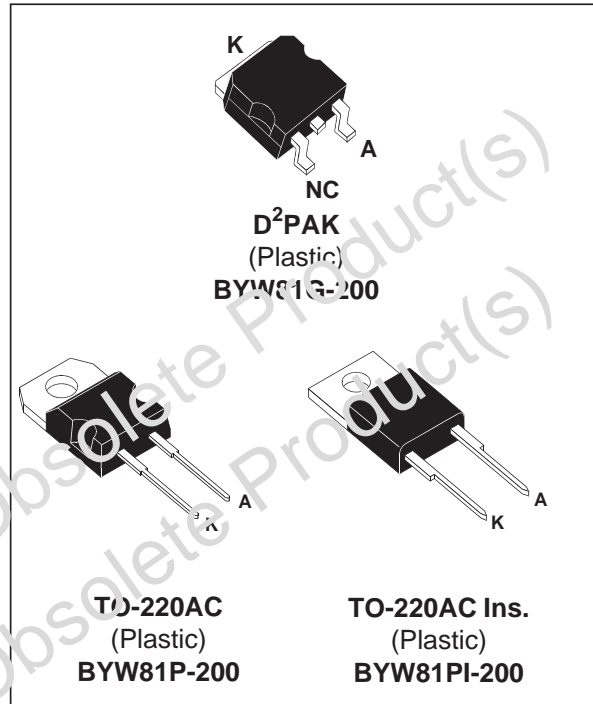
## HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

### FEATURES

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- INSULATED VERSION :  
Insulating voltage = 2500 V<sub>RMS</sub>  
Capacitance = 7 pF

### DESCRIPTION

Single chip rectifier suited for switchmode power supply and high frequency DC to DC converters. Packaged in TO-220AC and D<sup>2</sup>PAK, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit	
I <sub>F(RMS)</sub>	RMS forward current		35	A	
I <sub>F(AV)</sub>	Average forward current δ = 0.5	BYW81P	T <sub>c</sub> =115°C	15	A
		BYW81PI/G	T <sub>c</sub> =90°C	15	
I <sub>FSM</sub>	Surge non repetitive forward current	tp=10ms sinusoidal	200	A	
T <sub>stg</sub> T <sub>j</sub>	Storage and junction temperature range		- 40 to + 150 - 40 to + 150	°C °C	

Symbol	Parameter	Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage	200	V

**BYW81P-200 / BYW81PI-200 / BYW81G-200**

**THERMAL RESISTANCE**

Symbol	Parameter		Value	Unit
Rth (j-c)	Junction to case	BYW81P	2.0	°C/W
		BYW81PI / G	3.5	

**ELECTRICAL CHARACTERISTICS  
STATIC CHARACTERISTICS**

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> *	T <sub>j</sub> = 25°C	V <sub>R</sub> = V <sub>RRM</sub>			20	μA
	T <sub>j</sub> = 100°C				1.5	mA
V <sub>F</sub> **	T <sub>j</sub> = 125°C	I <sub>F</sub> = 12 A			0.85	V
	T <sub>j</sub> = 125°C	I <sub>F</sub> = 25 A			1.05	
	T <sub>j</sub> = 25°C	I <sub>F</sub> = 25 A			1.15	

Pulse test :

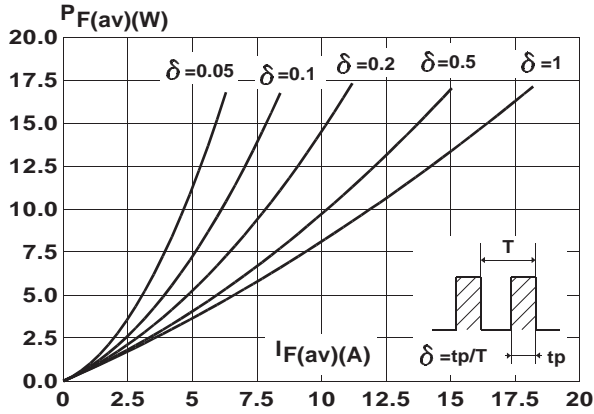
\* t<sub>p</sub> = 5 ms, duty cycle < 2 %

\*\* t<sub>p</sub> = 380 μs, duty cycle < 2 %

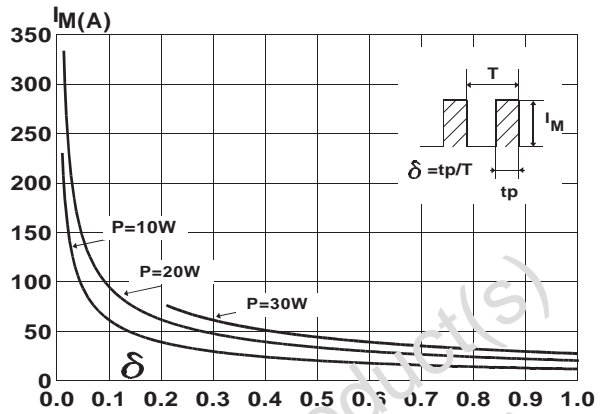
**RECOVERY CHARACTERISTICS**

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
trr	T <sub>j</sub> = 25°C	I <sub>F</sub> = 0.5A I <sub>R</sub> = 1A	I <sub>rr</sub> = 0.25A			25	ns
		I <sub>F</sub> = 1A V <sub>R</sub> = 30V	dI <sub>F</sub> /dt = -50A/μs			40	
tfr	T <sub>j</sub> = 25°C	I <sub>F</sub> = 1A V <sub>FR</sub> = 1.1 x V <sub>F</sub>	tr = 10 ns		15		ns
V <sub>FP</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 1A	tr = 10 ns		2		V

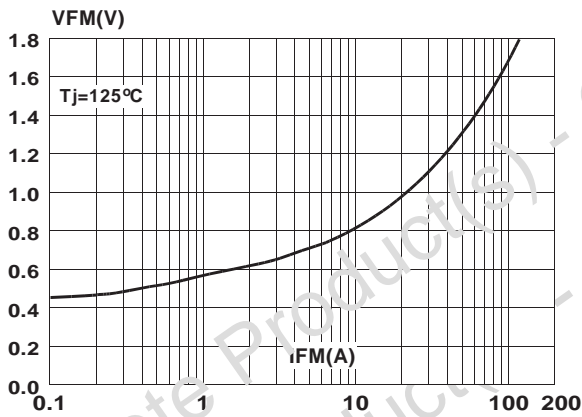
**Fig. 1:** Average forward power dissipation versus average forward current.



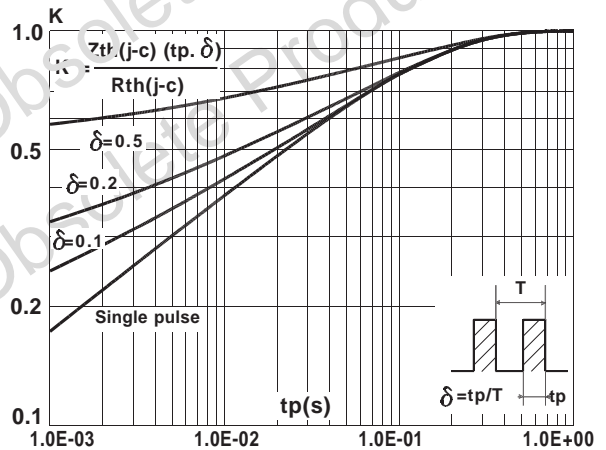
**Fig. 2:** Peak current versus form factor.



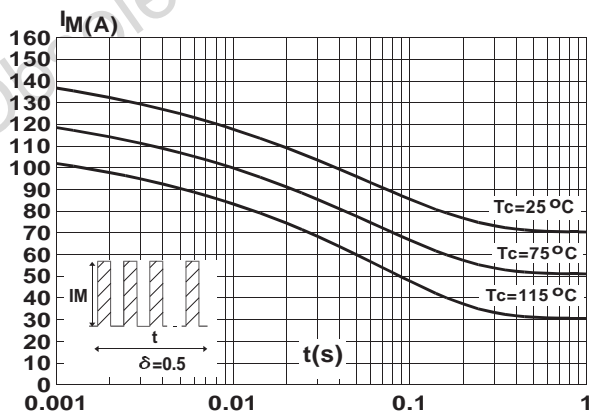
**Fig. 3:** Forward voltage drop versus forward current (maximum values).



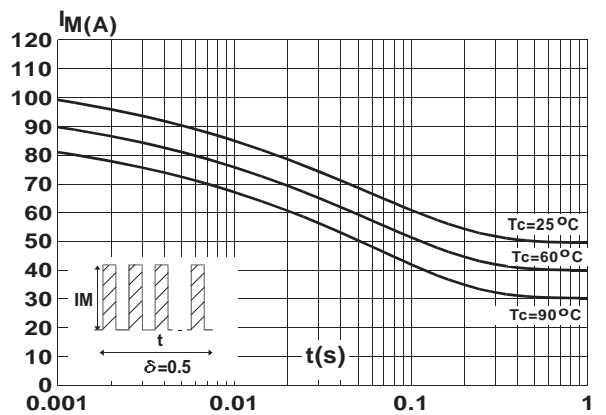
**Fig. 4:** Relative variation of thermal impedance junction to case versus pulse duration.



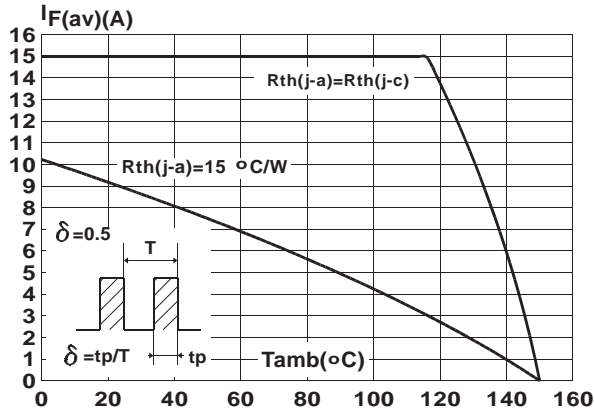
**Fig. 5:** Non repetitive surge peak forward current versus overload duration. (BYW81P)



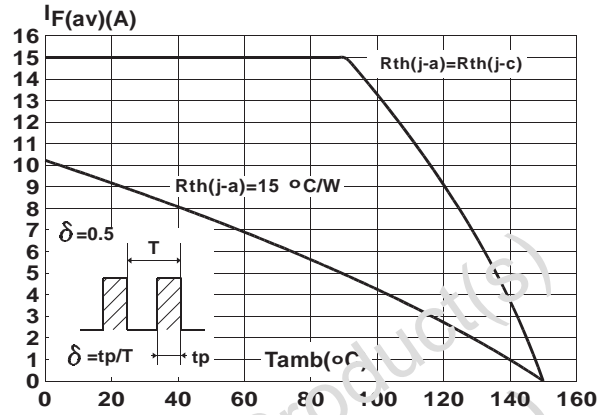
**Fig. 6:** Non repetitive surge peak forward current versus overload duration. (BYW81PI / BYW81G)



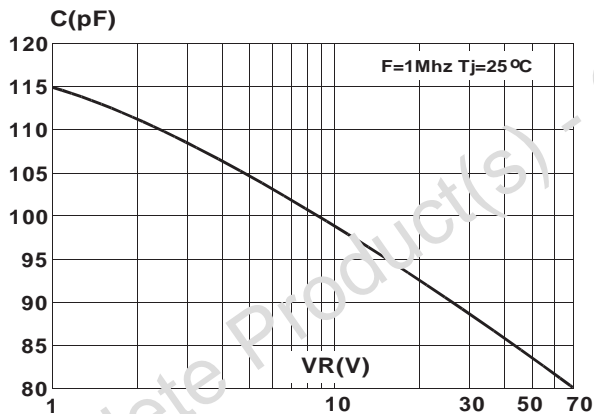
**Fig. 7:** Average current versus ambient temperature.  
(duty cycle : 0.5) (BYW81P)



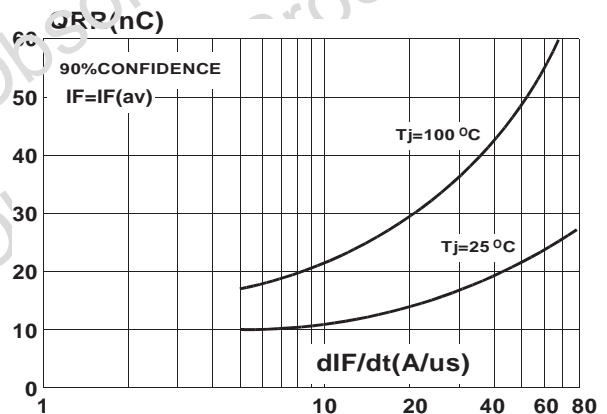
**Fig. 8:** Average current versus ambient temperature.  
(duty cycle : 0.5) (BYW81PI / BYW81G)



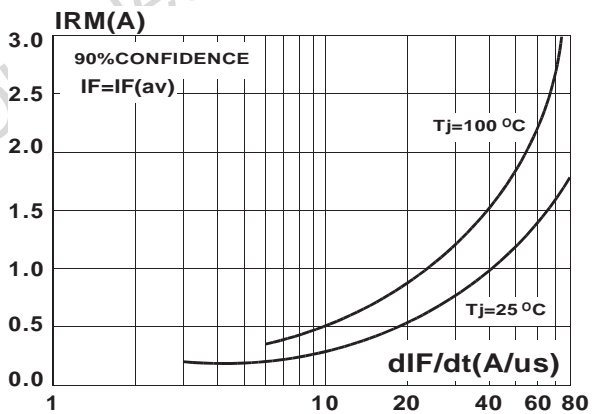
**Fig. 9:** Junction capacitance versus reverse voltage applied (Typical values).



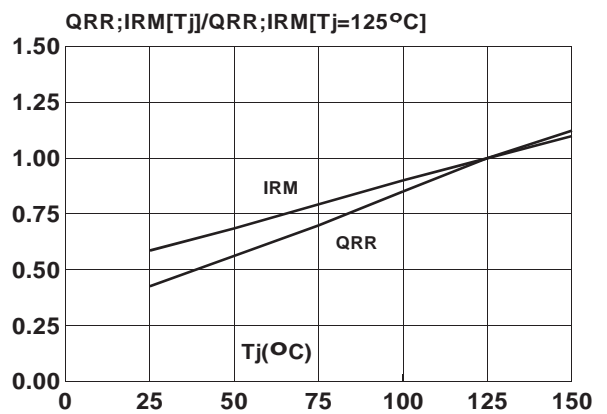
**Fig. 10:** Recovery charges versus  $dI_F/dt$ .



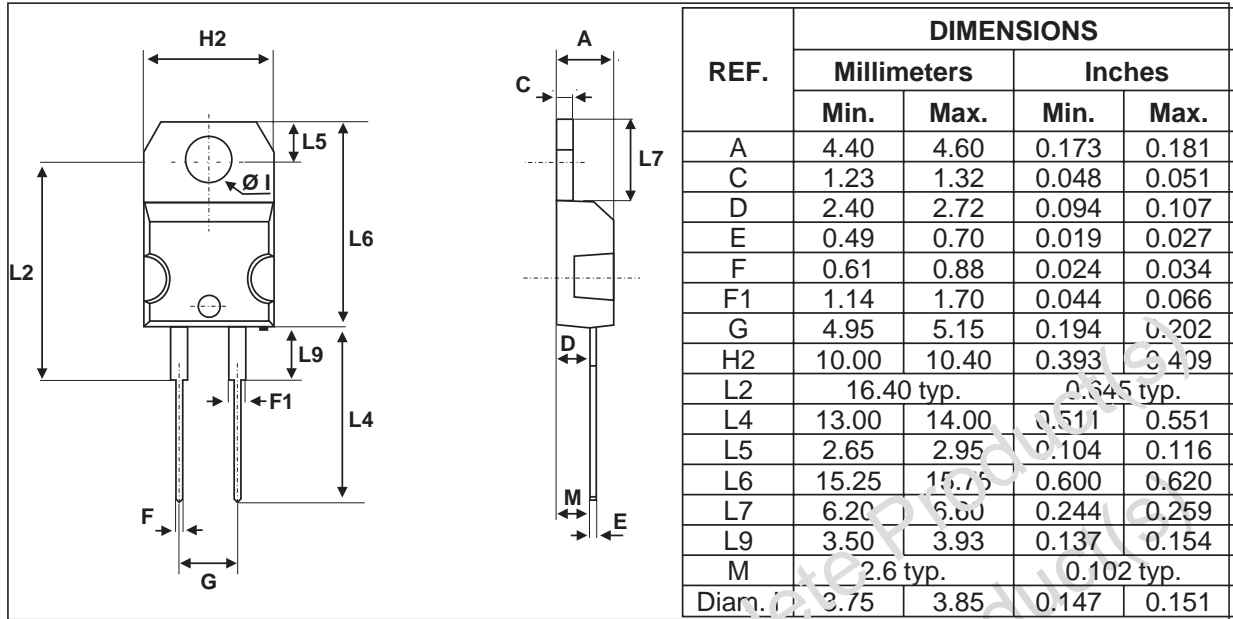
**Fig. 11:** Peak reverse current versus  $dI_F/dt$ .



**Fig. 12:** Dynamic parameters versus junction temperature.

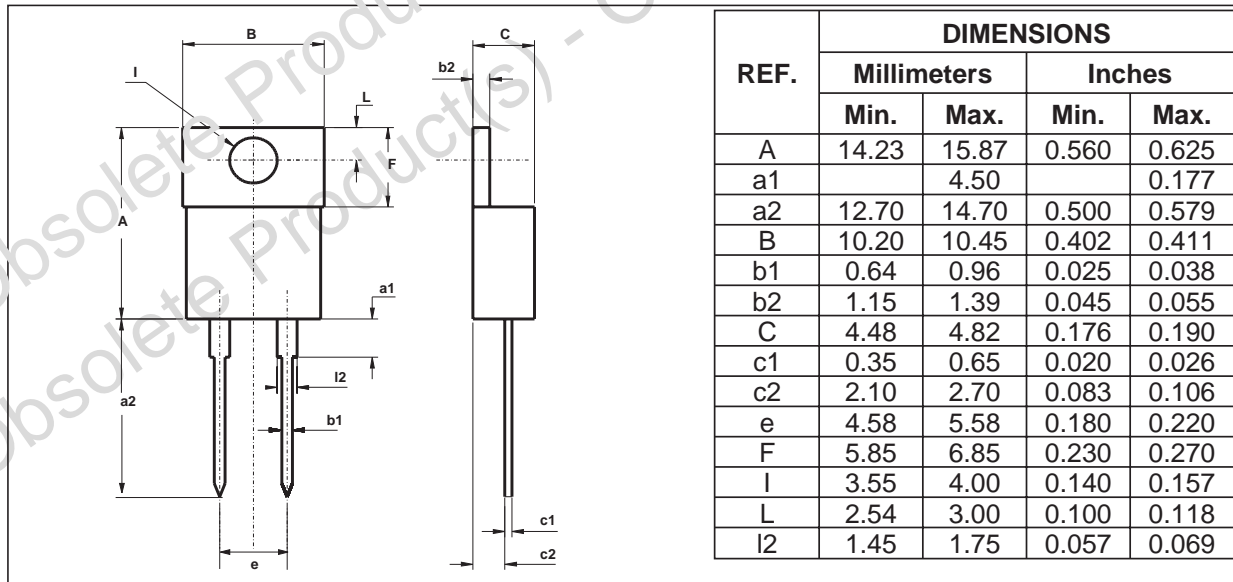


**PACKAGE MECHANICAL DATA**  
TO-220AC (JEDEC outline)



- **Marking** : Type number
- Cooling method : C
- Weight : 1.9 g
- Recommended torque value : 0.8m.N
- Maximum torque value : 1.0m.N

**PACKAGE MECHANICAL DATA**  
TO-220AC (isolated)



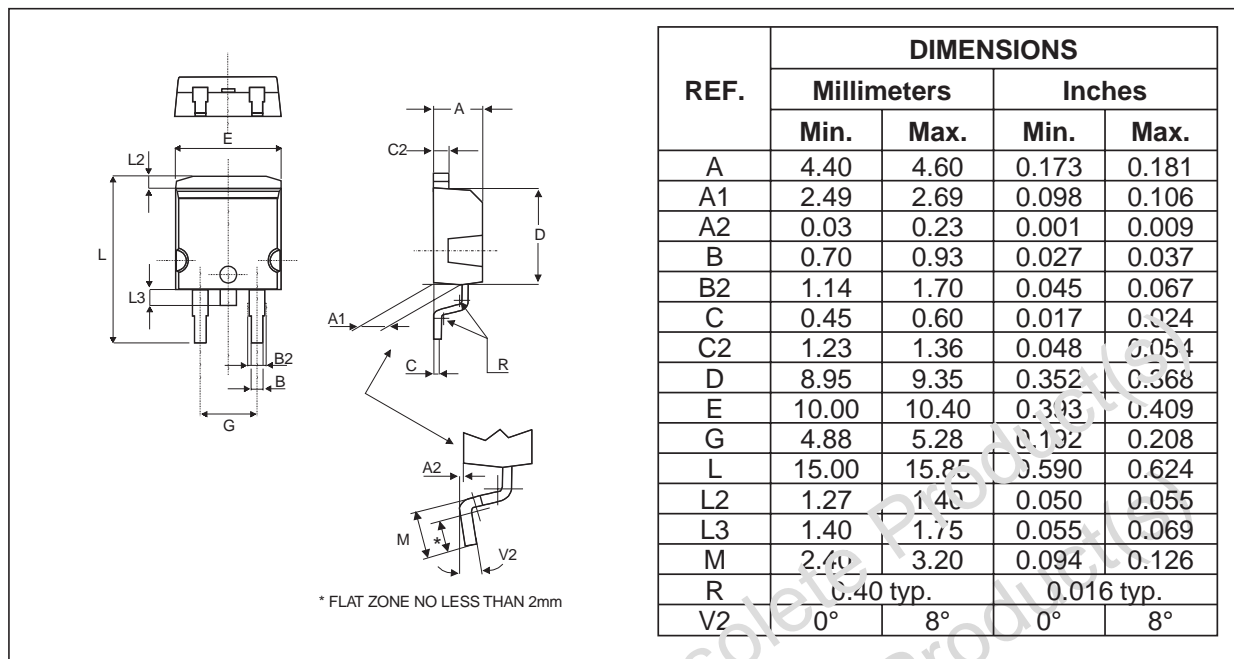
- **Marking** : Type number
- Cooling method : C
- Weight : 2.2 g
- Recommended torque value : 0.8m.N
- Maximum torque value : 1.0m.N



**BYW81P-200 / BYW81PI-200 / BYW81G-200**

**PACKAGE MECHANICAL DATA**

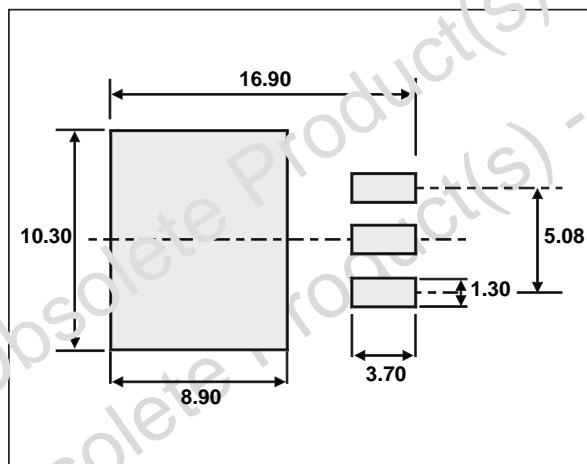
D<sup>2</sup>PAK (Plastic)



- Cooling method: by conduction (method C)

**FOOT PRINT DIMENSIONS (in millimeters)**

D<sup>2</sup>PAK



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics  
 © 2002 STMicroelectronics - Printed in Italy - All rights reserved.  
 STMicroelectronics GROUP OF COMPANIES  
 Australia - Brazil - Canada - China - Finland - France - Germany  
 Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore  
 Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>

